TECHNICAL DATA
DATA SHEET 316, REV -

THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: 1000 VOLT, 30 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^oC$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	1000	Vdc
Average DC Output Current (T_C = Case Temp) (I_o)	$T_C = 55^oC$ $T_C = 100^oC$ $T_C = 125^oC$	-	-	30 22 15	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^oC$ $T_A = 55^oc$ $T_A = 100^oc$	-	-	7.0 5.5 3.5	Amps
Peak Single Cycle Surge Current (I_{FSM})	t_p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	150	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_A = 25^oC$	-	-	75	Amps
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	°C
Maximum Forward Voltage (V_f)	I_f = 9.0A (300 µsec pulse, duty cycle < 2%)	-	-	1.4	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25°$ C $T_A = 100°$ C	-	-	5.0 100	µAmps
Reverse Recovery Time (t_{rr})	I_f = 0.5A, I_r = 1.0A, I_{rr} = 0.25A	-	-	5000	nsec
Thermal Resistance (θ_{JL})	-	-	-	1.25	°C/W

Note: Add a suffix **S** to the part number for **JAN-S Level Screening**.

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MECHANICAL DIMENSIONS: In Inches / mm

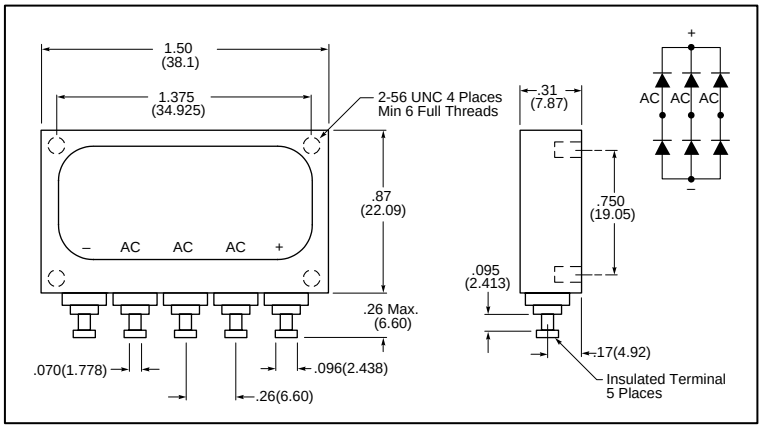


FIG. 406

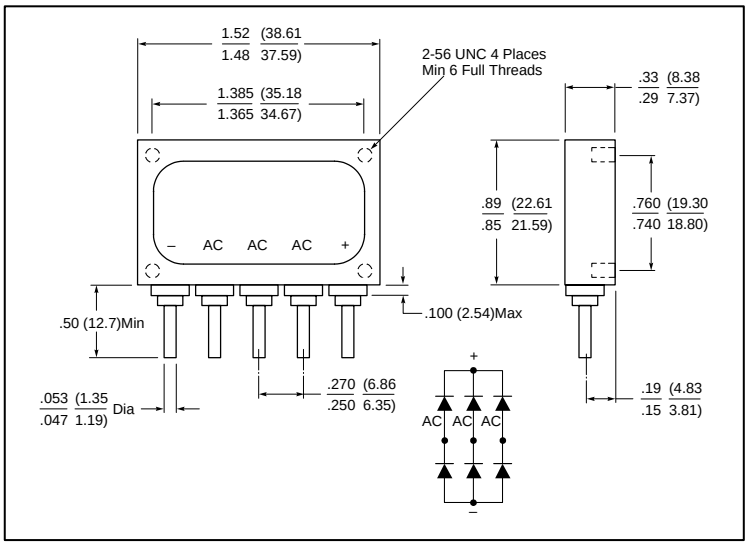


FIG. 406L

Note: Case finish - Black Anodized

TECHNICAL DATA

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